

United States Patent and Trademark Office



UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.usplo.gov

DATE MAILED: 11/01/2006

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/050,373	01/15/2002	Gurtej S. Sandhu	MI22-1896	7531
21567	7590 11/01/2006		EXAM	INER
WELLS ST. JOHN P.S.			SCHILLINGER, LAURA M	
601 W. FIRST AVENUE, SUITE 1300 SPOKANE, WA 99201)	ART UNIT	PAPER NUMBER
5. 5. 4. 4. 4.			2813	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)			
e e e e e	10/050,373	SANDHU ET AL.			
Office Action Summary	Examiner	Art Unit			
	Laura M. Schillinger	2813			
The MAILING DATE of this communication ap	,	the correspondence address			
Period for Reply	VIO OET TO EVEIDE AMON	NITU(O) OF THEFT (OO) FAVO			
A SHORTENED STATUTORY PERIOD FOR REPL WHICHEVER IS LONGER, FROM THE MAILING I Extensions of time may be available under the provisions of 37 CFR 1. after SIX (6) MONTHS from the mailing date of this communication. If NO period for reply is specified above, the maximum statutory period Failure to reply within the set or extended period for reply will, by statuly Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNICA .136(a). In no event, however, may a reply d will apply and will expire SIX (6) MONTH te, cause the application to become ABAN	ATION. y be timely filed S from the mailing date of this communication. IDONED (35 U.S.C. § 133).			
Status					
1) Responsive to communication(s) filed on 02 (<u> October 2006</u> .				
2a) This action is FINAL . 2b) ⊠ Thi	This action is FINAL . 2b)⊠ This action is non-final.				
	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is				
closed in accordance with the practice under	Ex parte Quayle, 1935 C.D. 1	1, 453 O.G. 213.			
Disposition of Claims					
4) Claim(s) 11-19 and 48-50 is/are pending in the 4a) Of the above claim(s) is/are withdra 5) Claim(s) is/are allowed. 6) Claim(s) 11-19 and 48-50 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or	awn from consideration.				
Application Papers					
9) The specification is objected to by the Examin 10) The drawing(s) filed on is/are: a) □ acc		the Evaminer			
Applicant may not request that any objection to the					
Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the E	ction is required if the drawing(s)	is objected to. See 37 CFR 1.121(d).			
Priority under 35 U.S.C. § 119	.xammer. Note the attached C	Mice Action of form F 10-132.			
a) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Bureat * See the attached detailed Office action for a list	nts have been received. Its have been received in Appority documents have been re Its u (PCT Rule 17.2(a)).	olication No ceived in this National Stage			
Attachment(s) 1) Notice of References Cited (PTO-892)	4) □ 1-4i 0	omani (PTO 412)			
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date 10/2/06. 	Paper No(s)/N	nmary (PTO-413) Mail Date rmal Patent Application			

. Application/Control Number: 10/050,373

Art Unit: 2813

DETAILED ACTION

Allowability is withdrawn due to newly discovered art.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 11-19 and 48-50 are rejected under 35 U.S.C. 102(e) as being anticipated by Moore ('543).

Moore teaches the following claimed limitations as cited below:

Claim 11 (previously presented): A method of forming a nitrogen-enriched region within a silicon-oxide-containing layer, comprising:

providing the silicon-oxide-containing layer over a substrate (Fig.3 (18));

the silicon-oxide- containing layer having a bare upper surface above the substrate and a lower surface on the substrate (Fig.3 (18));

exposing the silicon-oxide-containing layer to an activated nitrogen species from a nitrogen-containing plasma to introduce nitrogen into the silicon-oxide-containing layer and form a nitrogen-enriched region, the nitrogen-enriched region being only in an upper half of the silicon-oxide-containing layer (Fig.4 (22) and Col.3, lines: 25-35); and

. Application/Control Number: 10/050,373

Art Unit: 2813

thermally annealing the nitrogen within the nitrogen-enriched region, while the bare upper surface of the silicon-oxide-containing layer remains bare, to bond at least some of the nitrogen to silicon proximate the nitrogen; the nitrogen-enriched region remaining confined to the upper half of the silicon-oxide-containing layer during the annealing (Col.3, lines: 45-55).

Claim 12 (previously presented): The method of claim 11 wherein the nitrogen-enriched region is formed only in the upper third of the silicon-oxide-containing layer by the exposing (Col.3, lines: 30-40).

Claim13 (previously presented): The method of claim 11 wherein the nitrogen- enriched region is formed only in the upper third of the silicon-oxide-containing layer by the exposing and remains confined to the upper third of the silicon-oxide- containing layer during the annealing (Col.3, lines: 30-40).

Claim 14 (previously presented): The method of claim 11 wherein the nitrogen-enriched region is formed only in the upper fourth of the silicon-oxide-containing layer by the exposing and remains confined to the upper fourth of the silicon-oxide-containing layer during the annealing (Col.3, lines: 30-40).

Claim 15 (previously presented): The method of claim 11 wherein the nitrogen-enriched region is formed only in the upper fifth of the silicon-oxide-containing layer by the

- Application/Control Number: 10/050,373

Art Unit: 2813

exposing and remains confined to the upper fifth of the silicon-oxide- containing layer during the annealing (Col.3, lines: 30-40).

Claim 16 (previously presented): The method of claim 11 wherein the silicon-oxide-containing layer is maintained at a temperature of less than 200°C during the exposing (Col.3, lines: 54-55).

Claim 17 (original): The method of claim 11 wherein the plasma is maintained with a power of from about 500 watts to about 5000 watts during the exposing (Col.3, lines: 54-56).

Claim 18 (original): The method of claim 11 wherein the exposing occurs within a reactor, and wherein a pressure within the reactor is from about 5 mTorr to about 10 mTorr during the exposing (Col.3-4, lines: 55-20).

Claim 19 (original): The method of claim 11 wherein the exposing occurs for a time of less than or equal to about 1 minute (Col.3, lines: 55-65).

Claim 48 (previously presented): The method of claim 11 wherein the thermal annealing comprises thermal processing at a temperature of about 700°C for a time of about 30 seconds (Col.5, lines: 5-15).

Art Unit: 2813

Claim 49 (previously presented): The method of claim 11 wherein the thermal annealing comprises thermal processing at a temperature of about 1050°C for a time of about 5 seconds (Col.5, lines: 5-15).

Claim 50 (previously presented): The method of claim 11 wherein the thermal annealing comprises rapid thermal processing at a ramp rate of at least about 50°C/sec to a process temperature of less than 1000°C, with the process temperature being maintained for at least about 30 seconds (Col.5, lines: 5-15).

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Laura M. Schillinger whose telephone number is (571) 272-1697. The examiner can normally be reached on M-T, R-F 7:00-5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl W. Whitehead, Jr. can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Art Unit: 2813

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Xacca Nefolut

Laura M Schillinger Primary Examiner Art Unit 2813